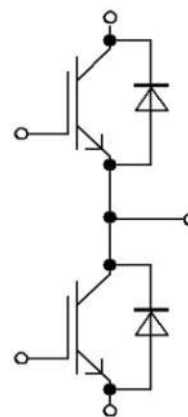


C2 series package: 1200V 600A IGBT module

Datasheet



Equivalent
Circuit Schematic

Features:

- Trenchgate Gen.7 IGBT technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High RBSOA capability
- Low static losses: $V_{CE(sat)} = 1,5V@25^{\circ}C$
- Low dynamic losses

Options:

- pre-applied TIM (option +M01)
- adoption for parallel connection (V_f selection)

Typical Applications:

- High Power Converters
- Motor Drives
- Uninterrupted Power Supply
- Photovoltaic

IGBT, Inverter / IGBT

Maximum Rated Values

Collector-emitter Voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
Continuous DC Collector Current		I_{Cnom}	600	A
	$T_C = 80^{\circ}\text{C}, T_{vj\ max} = 175^{\circ}\text{C}$	I_C	715	A
Repetitive Peak Collector Current	$I_{CRM} = 2 \times I_{Cnom}$	I_{CRM}	1200	A
Total Power Dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\ max} = 175^{\circ}\text{C}$	P_{tot}	2640	W
Gate-emitter Peak Voltage		V_{GES}	± 20	V

Characteristic Values

		min. typ. max.				
Collector-emitter Saturation Voltage ¹⁾	$I_C = 600\text{A}, V_{GE} = 15\text{V}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	V_{CEsat}		1.50 1.71 1.87 1.93	1.70	V
Gate Threshold Voltage	$V_{CE} = V_{GE}, I_C = 22.8\text{mA}, T_{vj} = 25^{\circ}\text{C}$	V_{GEth}	5.0	6.0	7.0	V
Gate Charge	$V_{GE} = -8\text{V}/15\text{V}, V_{CE} = 600\text{V}, T_{vj} = 25^{\circ}\text{C}$	Q_G	—	5.6	—	μC
Internal Gate Resistor	$T_{vj} = 25^{\circ}\text{C}$	R_{Gint}	—	0.85	—	Ω
Input Capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$ $f = 100\text{kHz}, T_{vj} = 25^{\circ}\text{C}$	C_{ies}	—	143	—	nF
Reverse Transfer Capacitance		C_{res}	—	0.35	—	nF
Collector-emitter Cutoff Current	$V_{CE} = 1200\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^{\circ}\text{C}$	I_{CES}	—	—	100	μA
Gate-emitter Leakage Current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^{\circ}\text{C}$	I_{GES}	—	—	100	nA
Turn-on Delay Time, Inductive Load	$I_C = 600\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = 15\text{V}/-8\text{V}$ $R_{gon} = 1.0\Omega$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	t_{don}	—	372 380 380 390	—	ns
Rise Time, Inductive Load	$I_C = 600\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = 15\text{V}/-8\text{V}$ $R_{gon} = 1.0\Omega$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	t_r	—	78 91 95 100	—	ns
Turn-off Delay Time, Inductive Load	$I_C = 600\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = 15\text{V}/-8\text{V}$ $R_{Goff} = 1.0\Omega$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	t_{doff}	—	593 635 635 650	—	ns
Fall Time, Inductive Load	$I_C = 600\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = 15\text{V}/-8\text{V}$ $R_{Goff} = 1.0\Omega$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	t_f	—	89 156 168 190	—	ns
Turn-on Energy Loss per Pulse	$I_C = 600\text{A}, V_{CE} = 600\text{V},$ $L_{\sigma} = 40\text{nH}, V_{GE} = 15\text{V}/-8\text{V},$ $R_{Gon} = 1.0\Omega, di/dt =$ $4100\text{A}/\mu\text{s} (T_{vj} = 175^{\circ}\text{C})$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	E_{on}	—	48.2 70.0 74.0 82.0	—	mJ
Turn-off energy Loss per Pulse	$I_C = 600\text{A}, V_{CE} = 600\text{V},$ $L_{\sigma} = 40\text{nH}, R_{Goff} = 1.5\Omega$ $V_{GE} = 15\text{V}/-8\text{V}, dv/dt =$ $4200\text{V}/\mu\text{s} (T_{vj} = 175^{\circ}\text{C})$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	E_{off}	—	50.7 68.0 70.0 74.0	—	mJ

SC Data	VCE = 600V, VGE = 15V/-8V	tp ≤ 8us, Tvj=25°C	Isc			3450	A
		tp ≤ 8us, Tvj=150°C				2650	
Thermal Resistance, Junction to Case	Per IGBT / IGBT		RthJC	—	0.056	—	K/W
Temperature under Switching Conditions ²⁾			Tvj op	-40		175	°C

Diode, Inverter Maximum Rated Values

Repetitive Peak Reverse Voltage	Tvj = 25°C	VRRM	1200	V
Continuous DC Forward Current		IF	600	A
Repetitive Peak Forward Current	ICRM = 2 x Ifnom	IFRM	1200	A

Characteristic Values

			min. typ. max.			
Forward Voltage ¹⁾	IF = 600A, VGE = 0V	Tvj = 25°C Tvj = 125°C Tvj = 150°C Tvj = 175°C	VF		1.90 1.87 1.80 1.72	2.40 — — — V
Peak Reverse Recovery Current	IF = 600A, VR = 600V -diF/dt = 6300A/us (Tvj = 175°C) VGE = -8V	Tvj = 25°C Tvj = 125°C Tvj = 150°C Tvj = 175°C	IRM	—	300 360 370 385	— — — — A
Recovery Charge	IF = 600A, VR = 600V -diF/dt = 6300A/us (Tvj = 175°C) VGE = -8V	Tvj = 25°C Tvj = 125°C Tvj = 150°C Tvj = 175°C	QR	—	28.0 56.5 67.5 79.5	— — — — uC
Reverse Recovery Energy	IF = 600A, VR = 600V -diF/dt = 6300A/us (Tvj = 175°C) VGE = -8V	Tvj = 25°C Tvj = 125°C Tvj = 150°C Tvj = 175°C	Erec	—	13.0 27.0 33.5 40.0	— — — — mJ
Thermal Resistance, Junction to Case	Per Doide / Diode		RthJC	—	0.082	— K/W
Temperature under Switching Conditions ²⁾			Tvj op	-40	—	175 °C

Module

Isolation Test Voltage	RMS, f = 50Hz, t = 1min	VISOL	3.0	kV
Material of Module Baseplate			Cu	
Internal Isolation	(class 1, IEC 61140) Basic insulation (class 1, IEC 61140)		AL2O3	
Creepage Distance	Terminal to heatsink Terminal to terminal		29.0 23.0	mm
Clearance	Terminal to heatsink Terminal to terminal		23.0 11.0	mm
Comparative Tracking Index		CTI	>200	

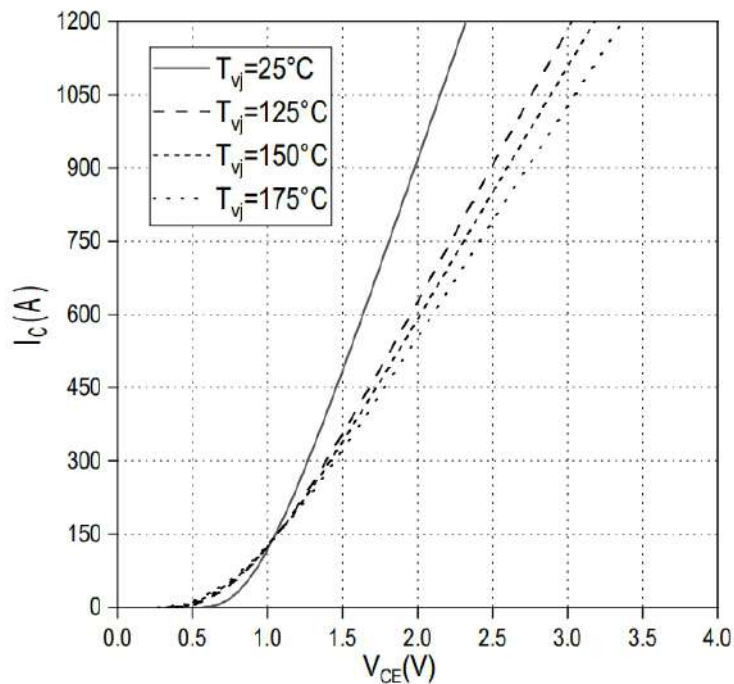
			min.	typ.	max.	
Stray Inductance Module		L _{sCE}	—	20	—	nH
Module Lead Resistance, Terminals-Chip	T _C = 25°C, Per Switch	R _{CC'+EE'}	—	0.50	—	mΩ
Storage Temperature		T _{stg}	-40	—	125	°C
Modul MountingTorque	M5	M	4.0	—	6.0	Nm
Terminal MountingTorque	M6	M	4.0	—	6.0	Nm
Weight		G	—	320	—	g

1) Terminal impedance is not included.

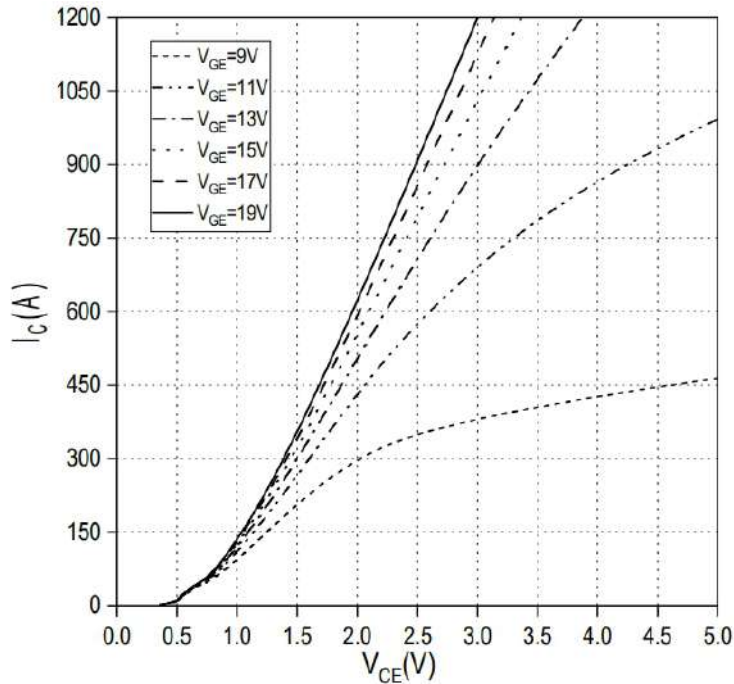
2) T_{vj op} > 150°C is allowed for operation at overload conditions.

Circuit Diagram

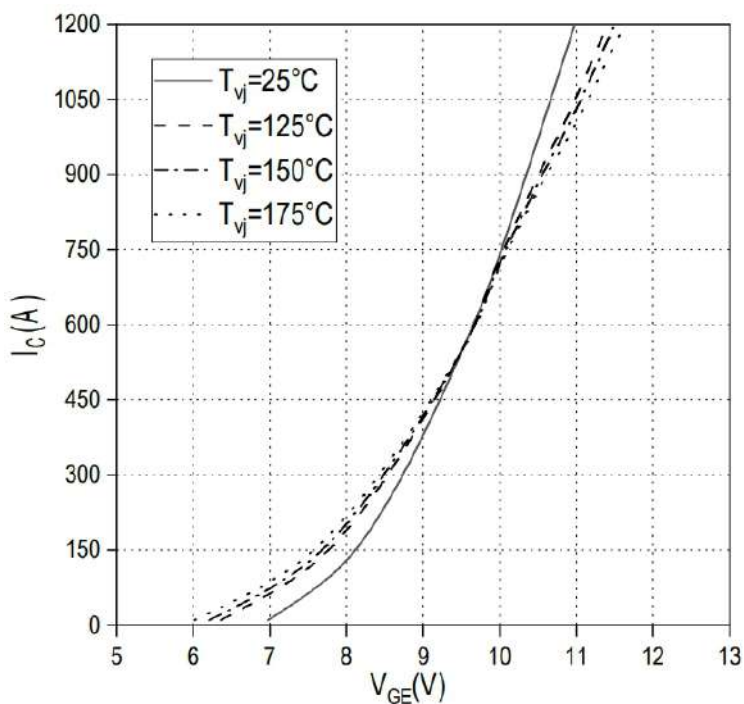
Output characteristic IGBT, Inverter (typical), IGBT
 $I_c = f(V_{CE})$, $V_{GE} = 15V$



Output characteristic IGBT, Inverter (typical), IGBT
 $I_c = f(V_{CE})$, $T_{vj} = 175^\circ C$

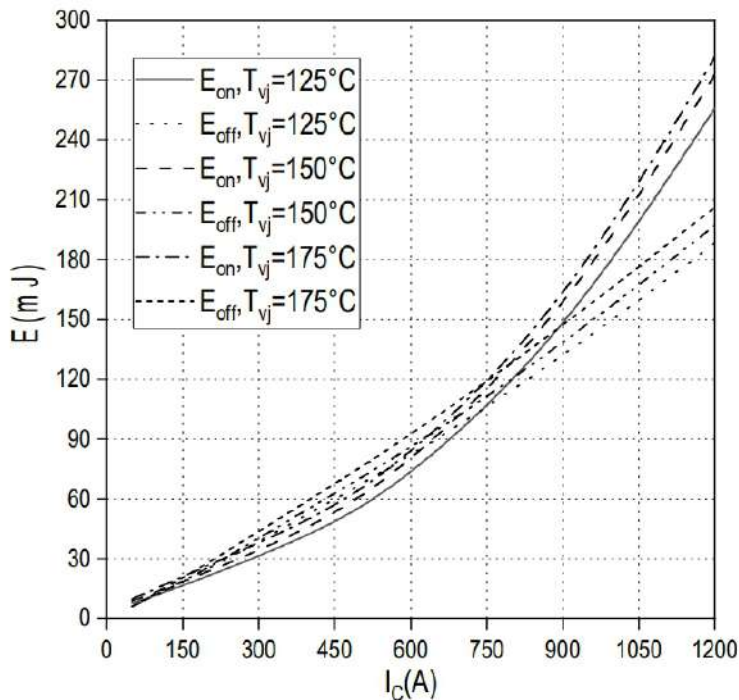


Transfer characteristic IGBT, Inverter (typical), IGBT
 $I_c = f(V_{GE})$, $V_{CE} = 20V$

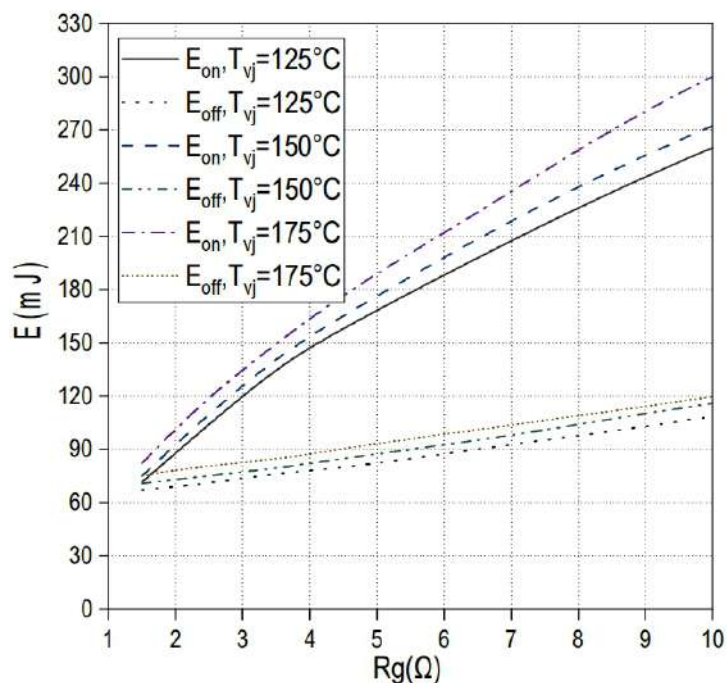


Switching losses IGBT, Inverter (Typical), IGBT

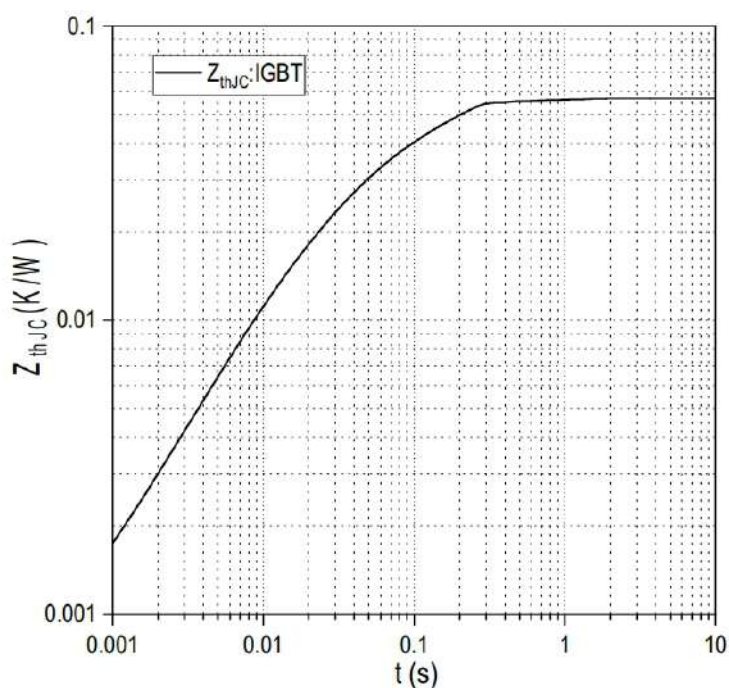
$E_{on} = f(I_c)$, $E_{off} = f(I_c)$
 $V_{GE} = 15V/-8V$, $R_{Gon} = 1.5\Omega$, $R_{Goff} = 4.7\Omega$, $V_{CE} = 600V$



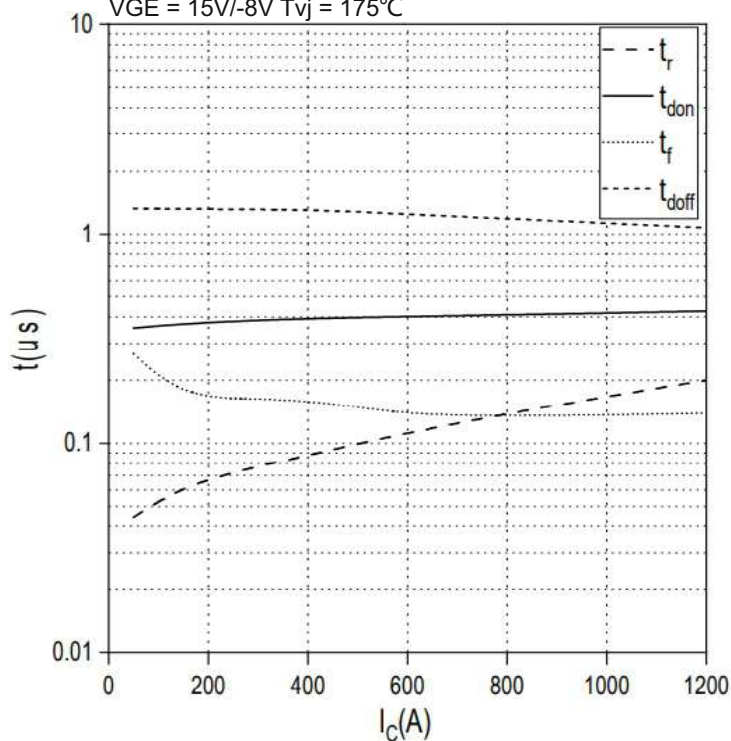
Switching losses IGBT, Inverter (typical), IGBT
 $V_{GE} = 15V/-8V$, $I_C = 600A$, $V_{CE} = 600V$



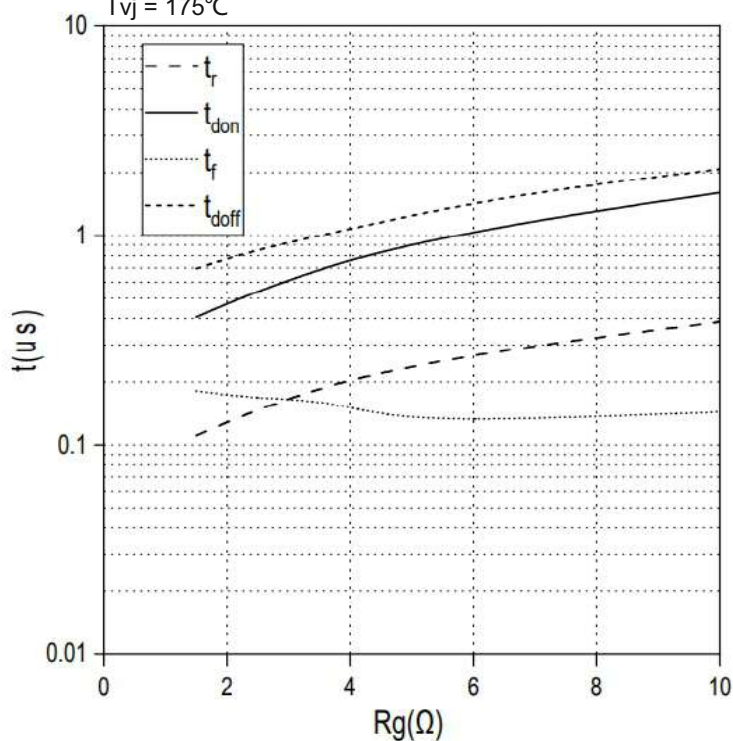
Transient thermal impedance IGBT, Inverter
 $Z_{thJC} = f(t)$



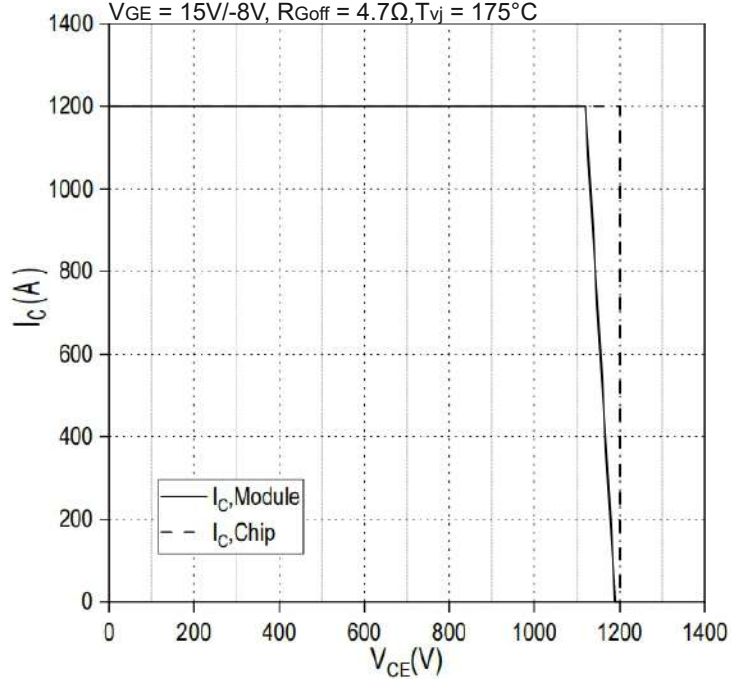
Switching time IGBT, Inverter (typical), IGBT
 $t = f(I_C)$
 $R_{goff} = 4.7\Omega$, $R_{gon} = 1.5\Omega$, $V_{CE} = 600V$
 $V_{GE} = 15V/-8V$, $T_{vj} = 175^\circ C$



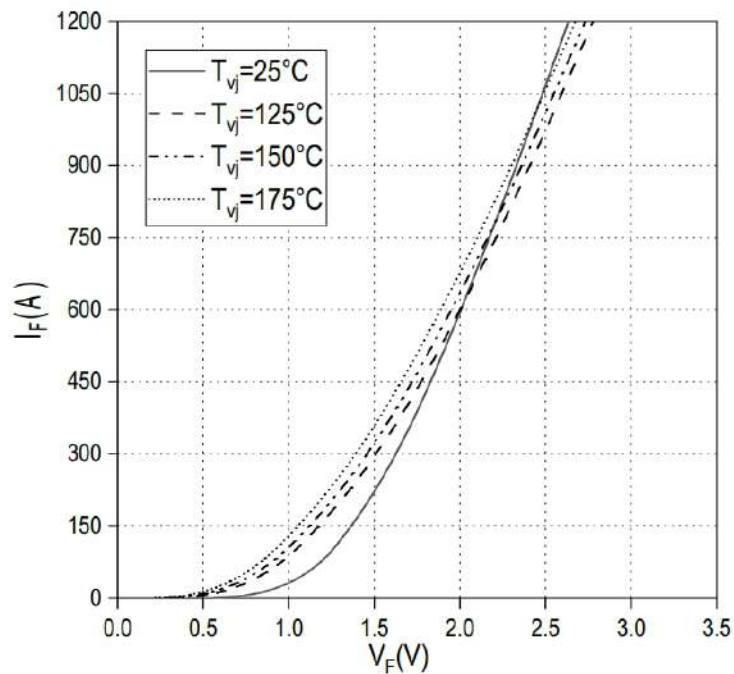
Switching time IGBT, Inverter (typical), IGBT
 $t = f(R_g)$
 $I_C = 600A$, $V_{CE} = 600V$, $V_{GE} = 15V/-8V$
 $T_{vj} = 175^\circ C$



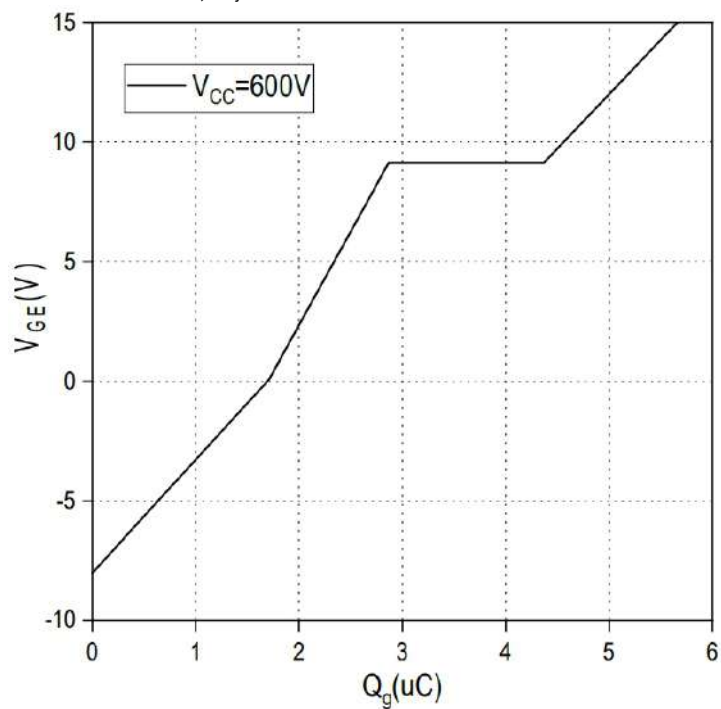
Reverse bias safe operating area IGBT, Inverter
(RBSOA) $I_C = f(V_{CE})$,
 $V_{GE} = 15V/-8V$, $R_{Goff} = 4.7\Omega$, $T_{vj} = 175^\circ C$



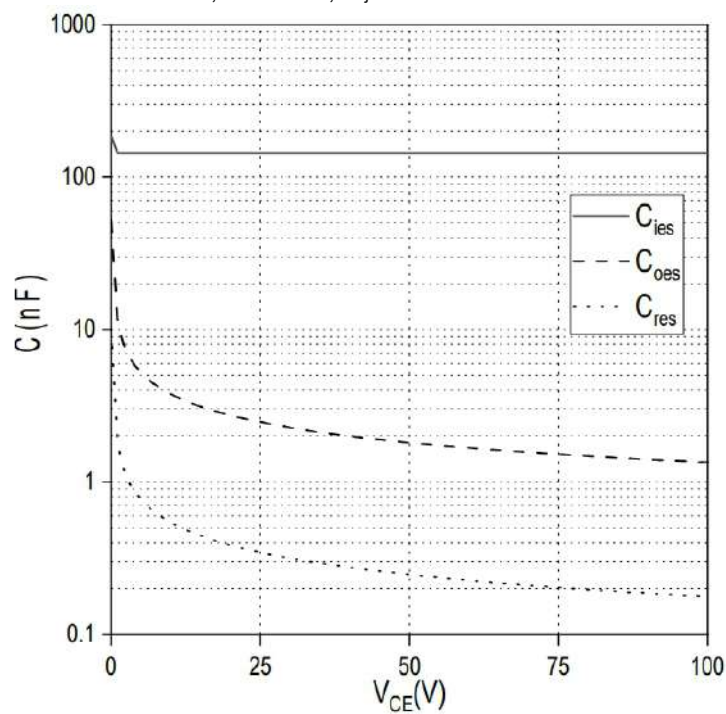
Forward characteristic of Diode, Inverter (typical)
 $I_F = f(V_F)$

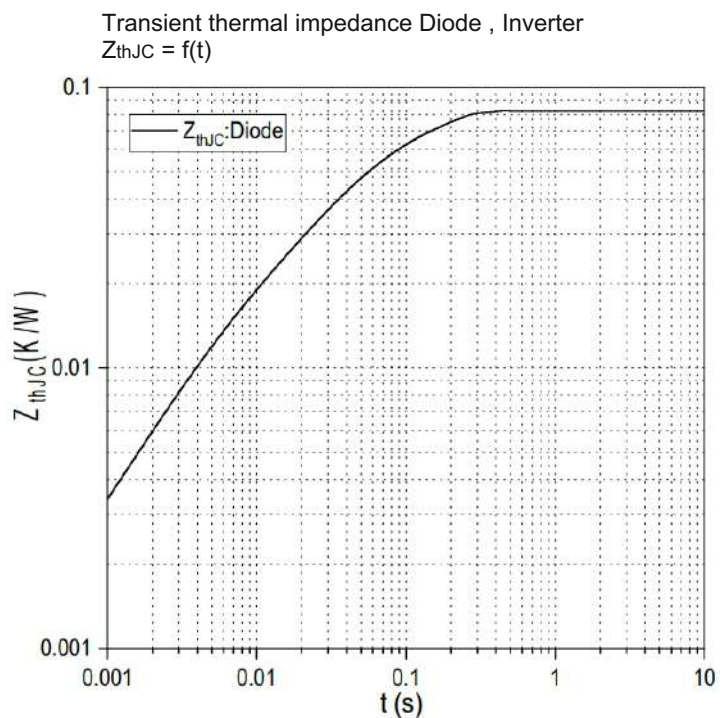
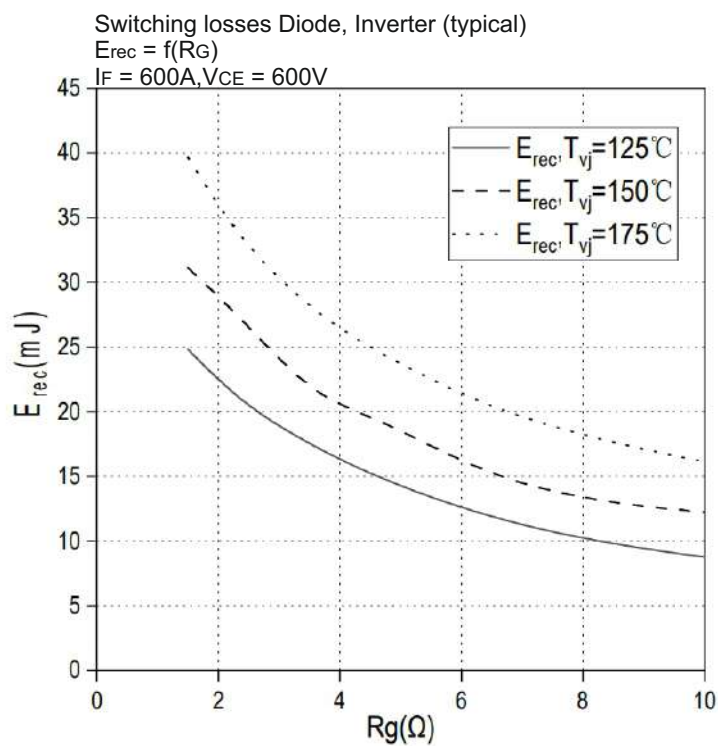
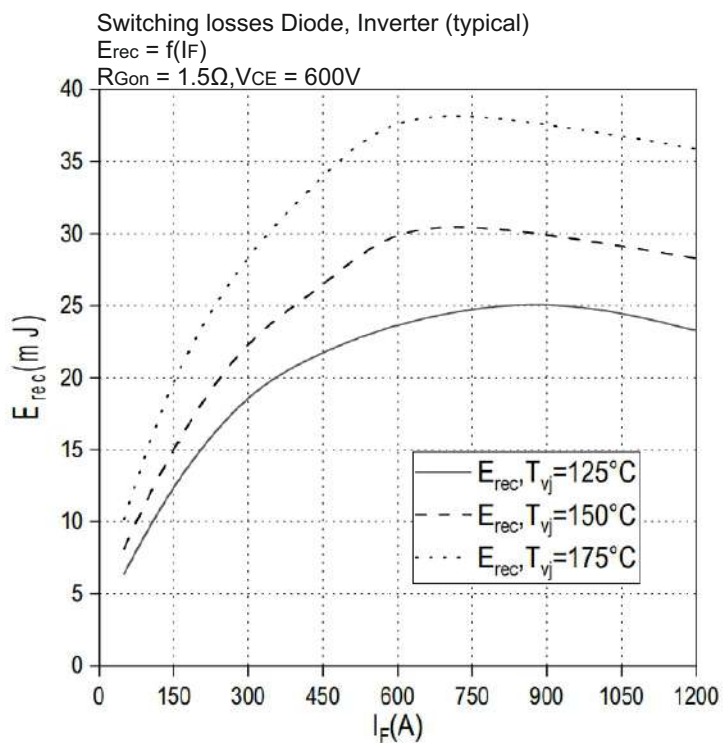


Gate charge characteristic, IGBT, Inverter (typical)
 $V_{GE} = f(Q_g)$
 $I_C = 600A$, $T_{vj} = 25^\circ C$



Capacity characteristic, IGBT, Inverter (typical)
 $C = f(V_{CE})$
 $f = 100kHz$, $V_{GE} = 0V$, $T_{vj} = 25^\circ C$





The circuit diagram shows a 2-to-4 decoder implemented with two 3-input NAND gates and two 2-input OR gates. The two input lines are labeled 6 and 7. The four output lines are labeled 2, 3, 4, and 5. The first 3-input NAND gate has inputs 1, 6, and 7, and its output is 2. The second 3-input NAND gate has inputs 2, 6, and 7, and its output is 3. The first 2-input OR gate has inputs 2 and 3, and its output is 4. The second 2-input OR gate has inputs 2 and 3, and its output is 5.

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